

FIG. 1
(PRIOR ART)

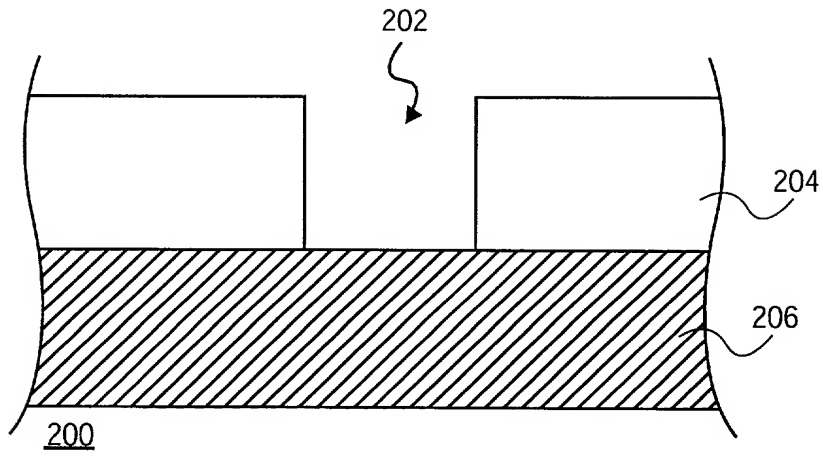


FIG. 2
(PRIOR ART)

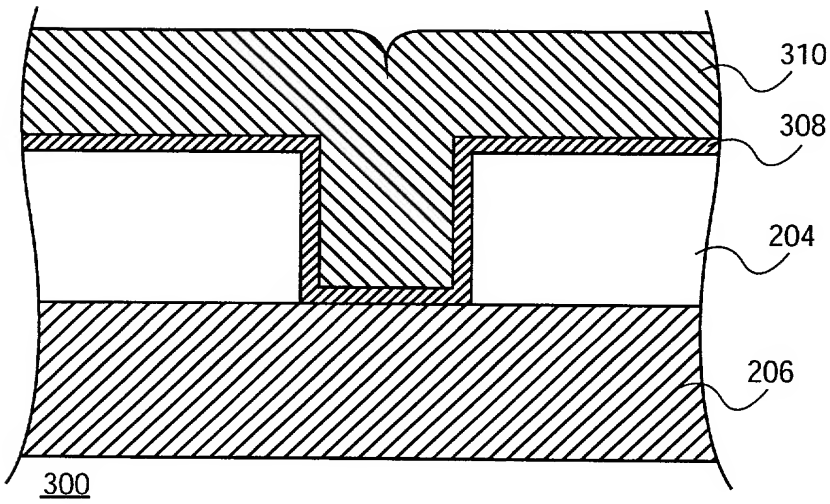


FIG. 3
(PRIOR ART)

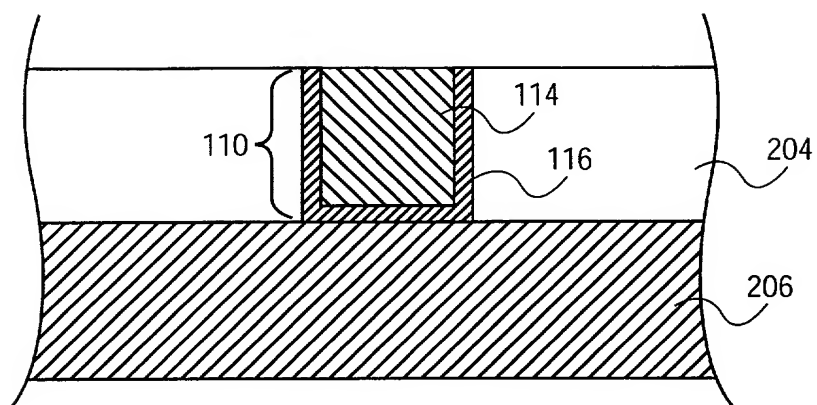
[illegible]

FIG. 4
(PRIOR ART)

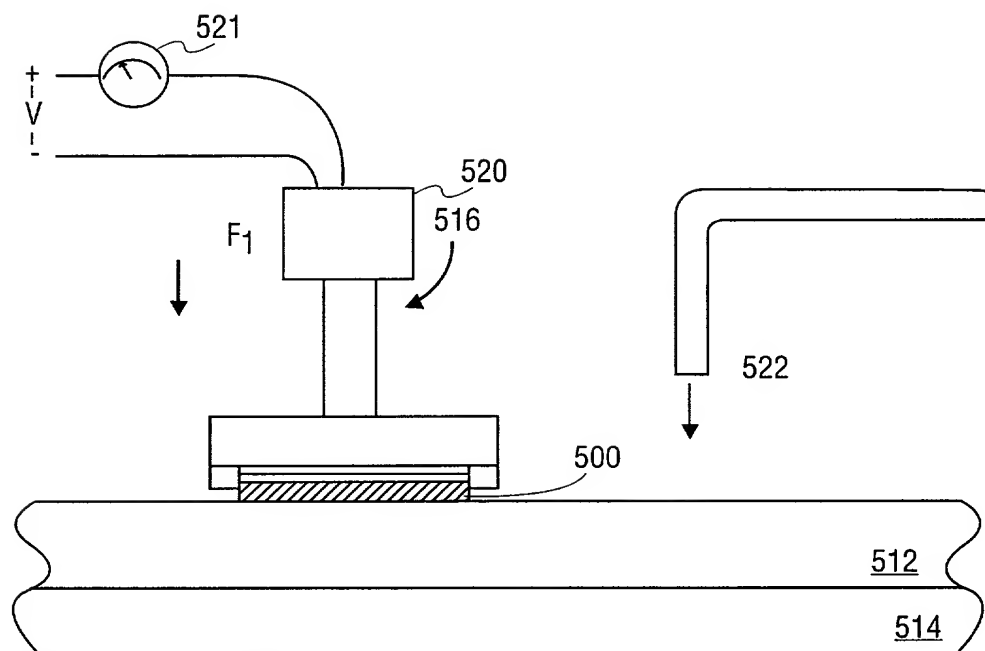


FIG. 5

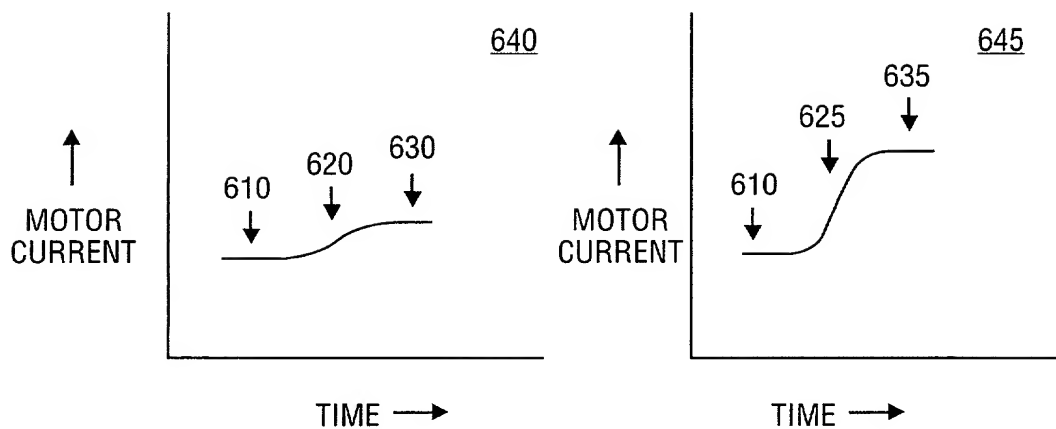


FIG. 6

REMOVING EXCESS VIA MATERIAL FROM
AN INTEGRATED CIRCUIT WAFER
BY CHEMICAL MECHANICAL POLISHING
THE WAFER WITH A SLURRY AND AN
OXIDATION AGENT FOR THE VIA
MATERIAL ON A SURFACE
710



MONITORING THE CURRENT REQUIRED TO
ROTATE THE WAFER ON THE SURFACE AS
A MEASURE OF THE EXCESS VIA
MATERIAL REMOVAL ENDPOINT
720



OPTIMIZING THE ENDPOINT SIGNAL BY
BUFFERING A SLURRY USED IN THE
CHEMICAL MECHANICAL POLISH
730

FIG. 7